

ABSTRACT

NONVOLATILE SEMICONDUCTOR MEMORY DEVICE AND METHOD FOR MANUFACTURING NONVOLATILE SEMICONDUCTOR MEMORY DEVICE

According to one embodiment, a part of a buried insulating film buried in a trench is removed; accordingly, an air gap is formed between adjacent floating gate electrodes in a word line direction, and the air gap is formed continuously along the trench in a manner of sinking below a control gate electrode.

FIG. 1